



Partial Translation of Extended Abstracts  
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High quality GaN film on low-temperature AlGaN  
buffer layer grown with high growth rate

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ER 287

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1. Introduction A GaN layer on sapphire is generally grown on a buffer layer grown at a low temperature, and it is important to optimize conditions of the buffer layer and the GaN layer grown thereon for improving the characteristics of a nitride-based light-emitting device. This time we have found out that a high-quality GaN film can be obtained by remarkably increasing the growth rate for a buffer layer, and report this.

2. Experiment GaN was grown on c-plane sapphire by atmospheric pressure MOCVD in a two-step growth method. A buffer layer was prepared from AlGaN, and growth temperatures for the buffer layer and the GaN layer grown thereon were 600°C and 1080°C respectively. The growth rate for the buffer layer



## Growth Conditions

### 1. Structure of MOCVD Apparatus

- ✓ 1-1. ~~Trilaminar~~ Horizontal MOCVD Apparatus  
*three layer etal flow*

- 1-2. Heating System by High-Frequency  
Oscillation

### 2. Growth Conditions for AlGaN Low-Temperature Buffer Layer

- ✓ 2-1. Substrate: ~~Sapphire C-Plane~~ Substrate  
*C-face*

- 2-2. Used Materials: TMA1, TMGa, NH3, H2 and N2

$$\text{TMA1} / (\text{TMA1} + \text{TMGa}) \doteq 0.5$$

- 2-3. Growth Temperature: 600°C

- 2-4. Thickness of Grown Film: 120 to 140 Å

### 3. Growth Conditions for GaN Layer

- 3-2. Used Materials: TMGa, NH3, H2 and N2

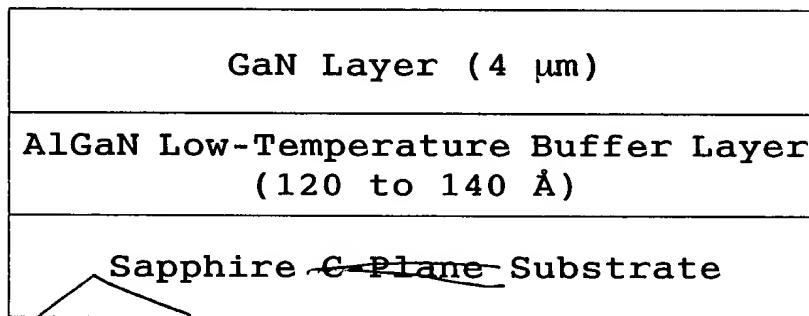
- 3-2. Growth Temperature: 1080°C

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## Structure of and Method of Evaluation for Evaluated Sample

### Structure of Evaluated Sample



### Evaluation Method

1. Full Width at Half Maximum in X-Ray Diffraction Rocking Curve

GaN(0002) Diffraction

2. Etch Pit Density

Etching Method NaOH:KOH = 5:1 (280°C)

3. Sectional TEM Observation

✓ *Observations of etch pits in GaN layers*  
(1) "Evaluation of Defects by Etch Pit in GaN" by Masayuki Hata et. al., Sanyo Electric Co., Ltd. Microelectronics Research Center

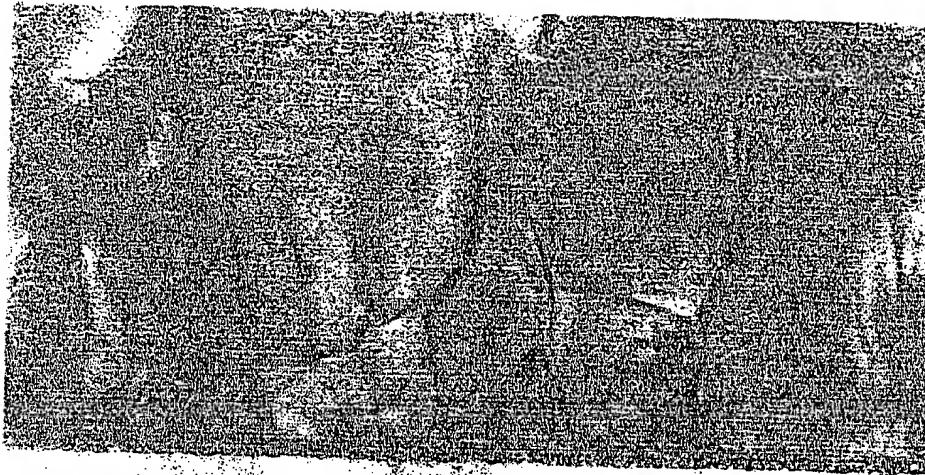
Extended Abstracts of the 57<sup>th</sup> Meeting of the Japan Society of Applied Physics (1996), No. 1, p. 302

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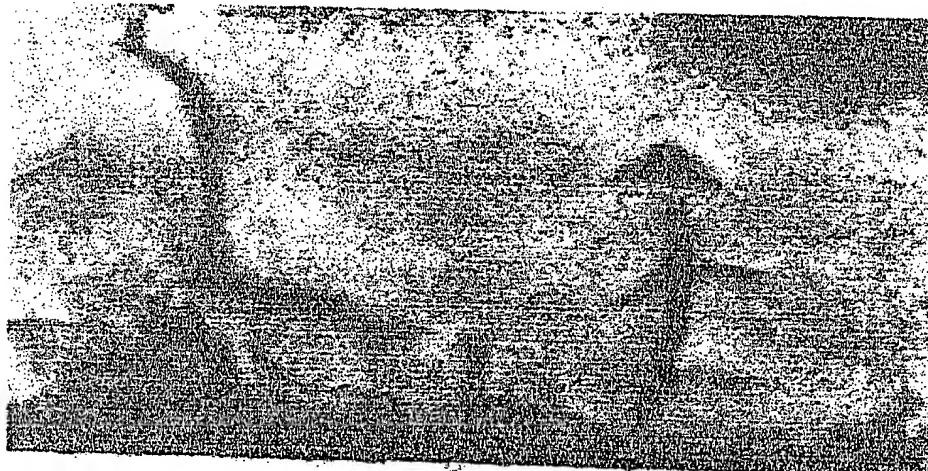
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Growth Rate: 6.7 Å/sec.



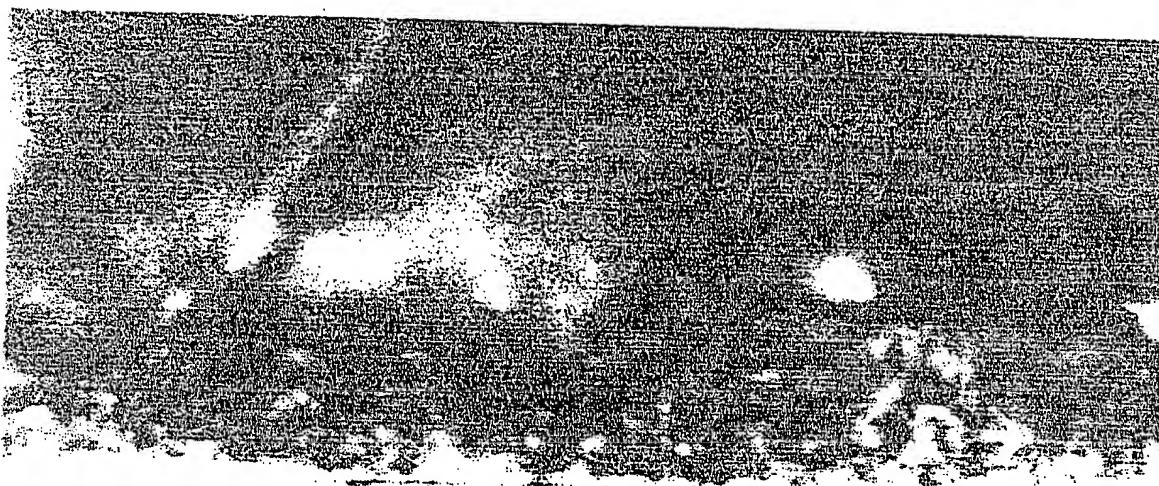
Growth Rate: 25.0 Å/sec.

Sectional TEM Photograph of Interface Between  
Sapphire Substrate and GaN Layer ( $\times 300,000$ )

[Sectional Photograph on GaN (11-20) Plane  
face ✓

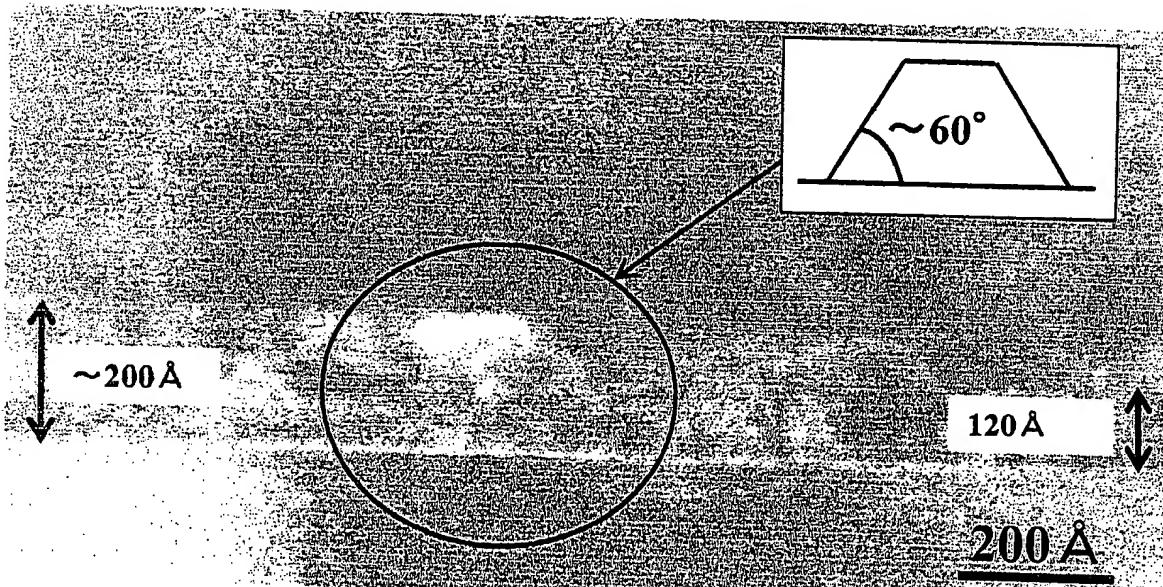
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200 Å

Growth Rate: 6.7 Å/sec.



Growth Rate: 25.0 Å/sec.

- Sectional TEM Photograph of Interface Between  
Sapphire Substrate and GaN Layer ( $\times 2,000,000$ )  
[Sectional Photograph on GaN (11-20) plane] *face* ✓

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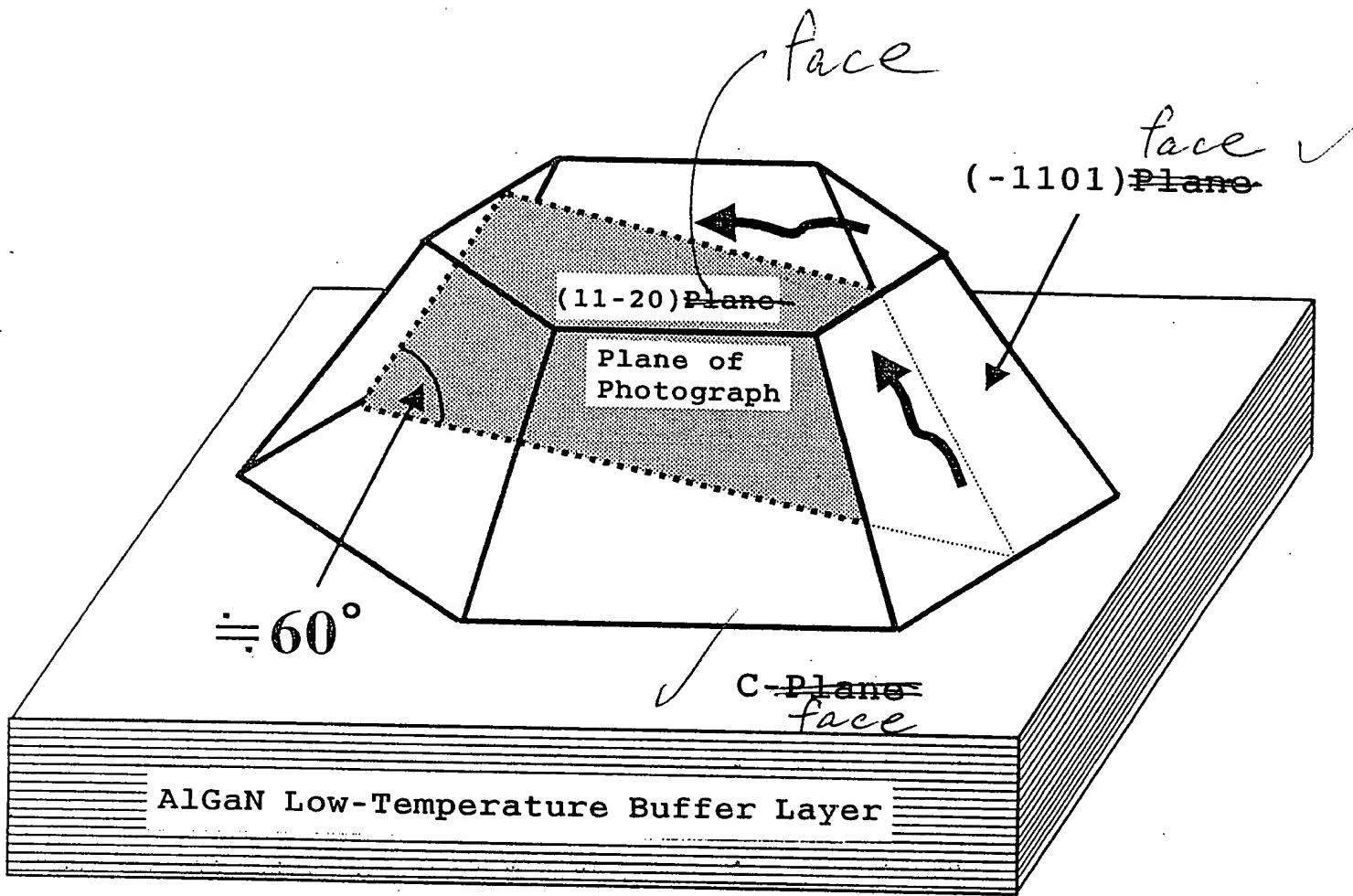


Image Diagram of Direction of Defect in Initial State of Growth of GaN Layer Employing Fast-Grown AlGaN Low-Temperature Buffer Layer

## Conclusion

1. Increasing growth rate of AlGaN low-temperature buffer layer to 25 to 30 Å/sec.

### GaN Layer

- Full Width at Half Maximum of X-Ray Rocking Curve: 250 sec.
- Etch Pit Density:  $1.0 \times [10^9 \text{ cm}^{-2}]$



From sectional TEM on the interface between sapphire and GaN:

- ① Most of defects caused on the interface progress in directions parallel to the (-1101) ~~plane~~ and the C-plane.

*face*                   *face*  
                            ↓

- ② The number of through defects in the C-axis direction decreases.

2. A blue semiconductor laser of room-temperature continuous oscillation was obtained through high-quality GaN growth.